

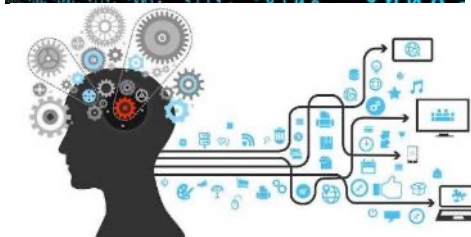
**A 1 kW eGaN
FET-based LLC
Resonant
Converter in a
 $\frac{1}{8}$ th Power
Brick Size**

Market Trends Leading to 48V Rack Power Architecture

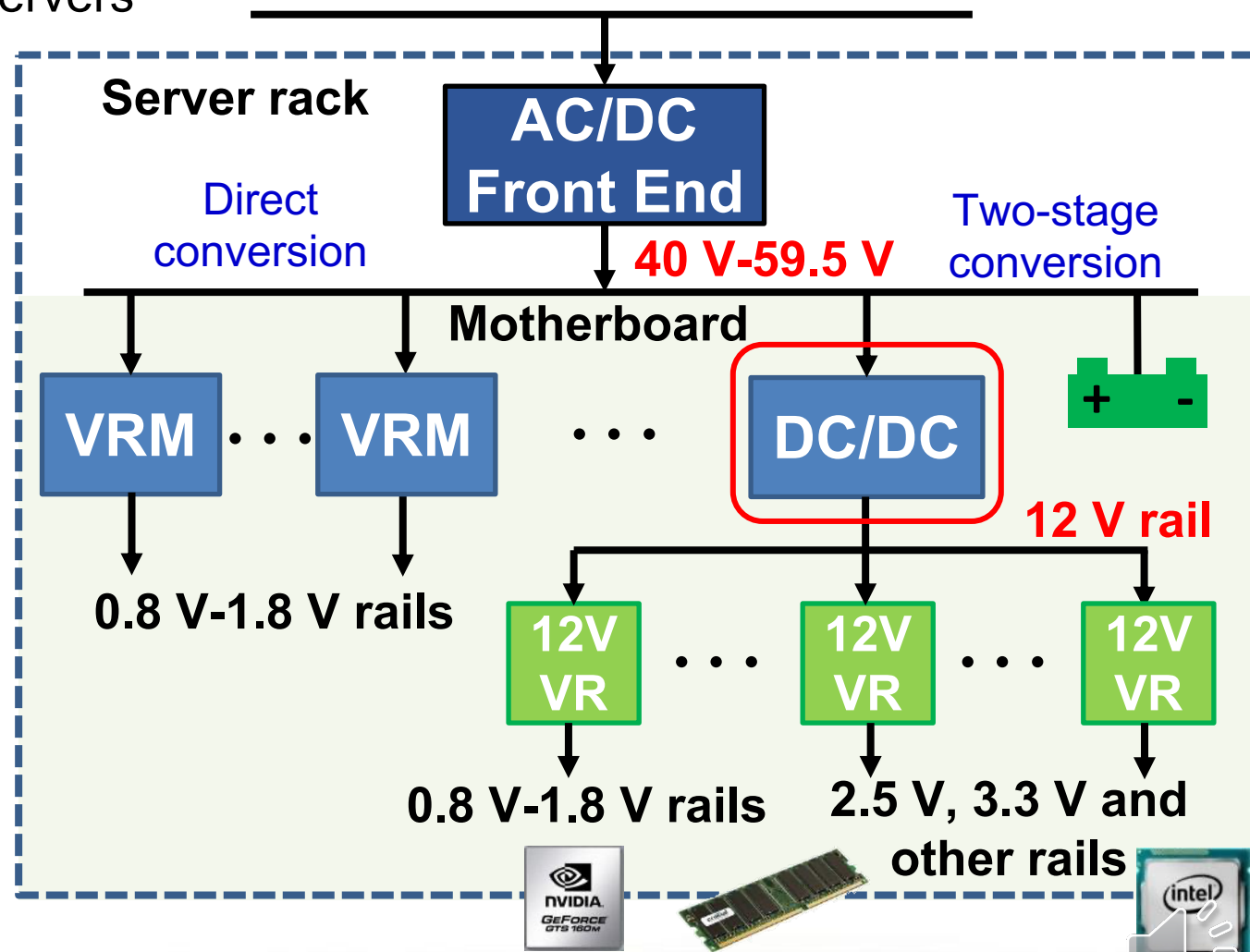
AI adoption, 5G, Big Data, Cloud Servers



- High power demand
- Higher power per board
- Higher component density



- Migration to on board 48V
- Premium for density

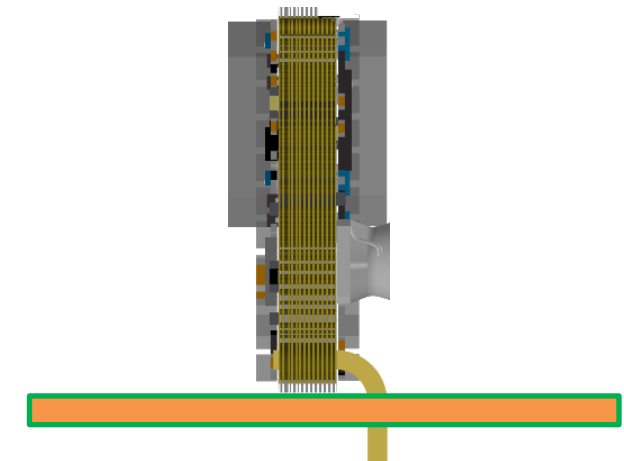


Specification	Min.	Nom.	Max.	Units
Input Voltage	36	48	60	Volts
Output Voltage	9	12	15	Volts
Output Power		1000		Watt
Switching frequency		1		MHz
Total thickness			*10	mm
Cooling Air-Flow			400	LFM
Size (X & Y)			‡58.4 x 22.9	mm

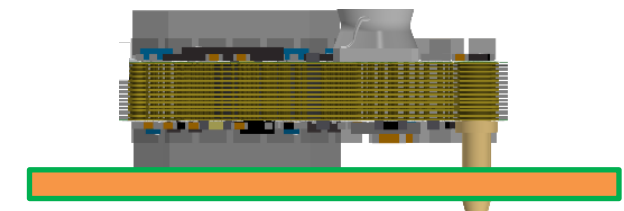
‡ Standard DOSA 1/8th Brick converter size

* Excluding heatsink

- Horizontal or Vertical mount using pins

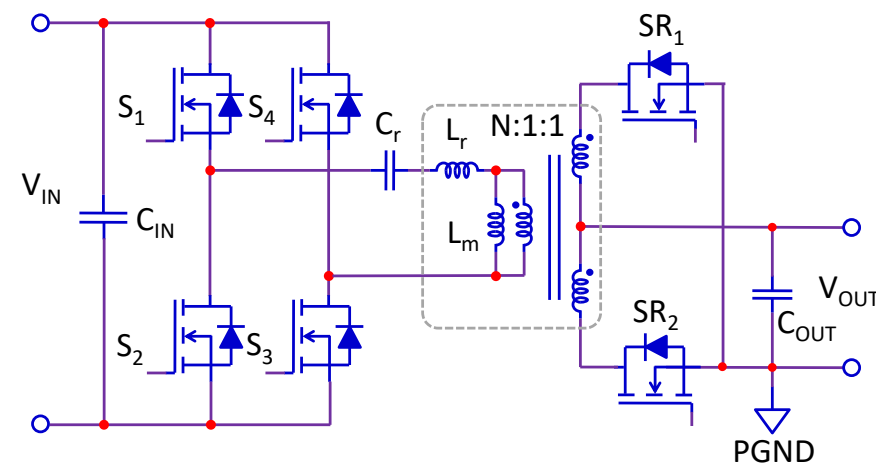
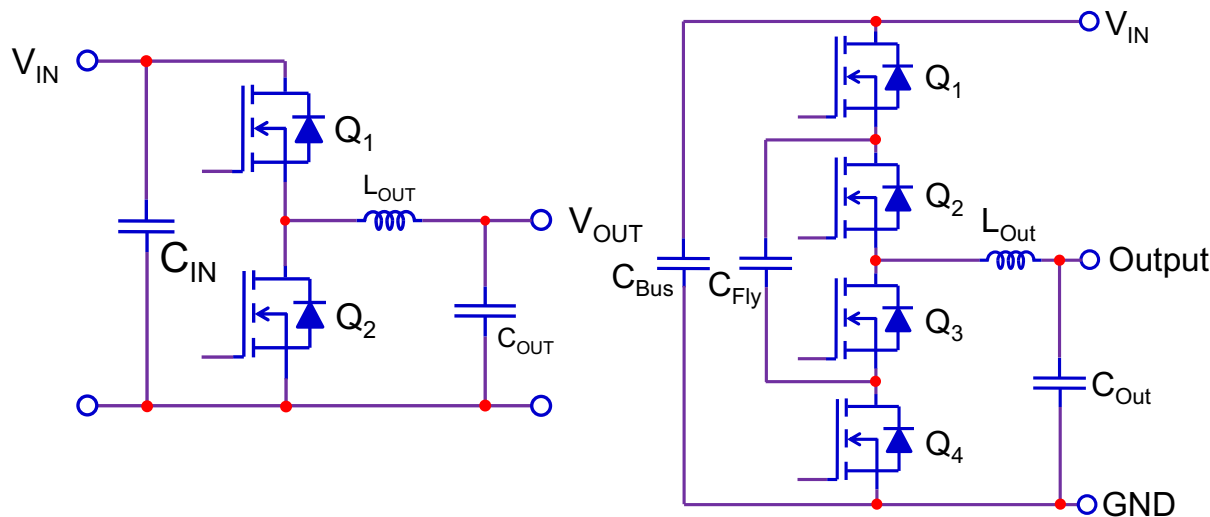


Vertical mount



Horizontal mount

Topology Down Selection



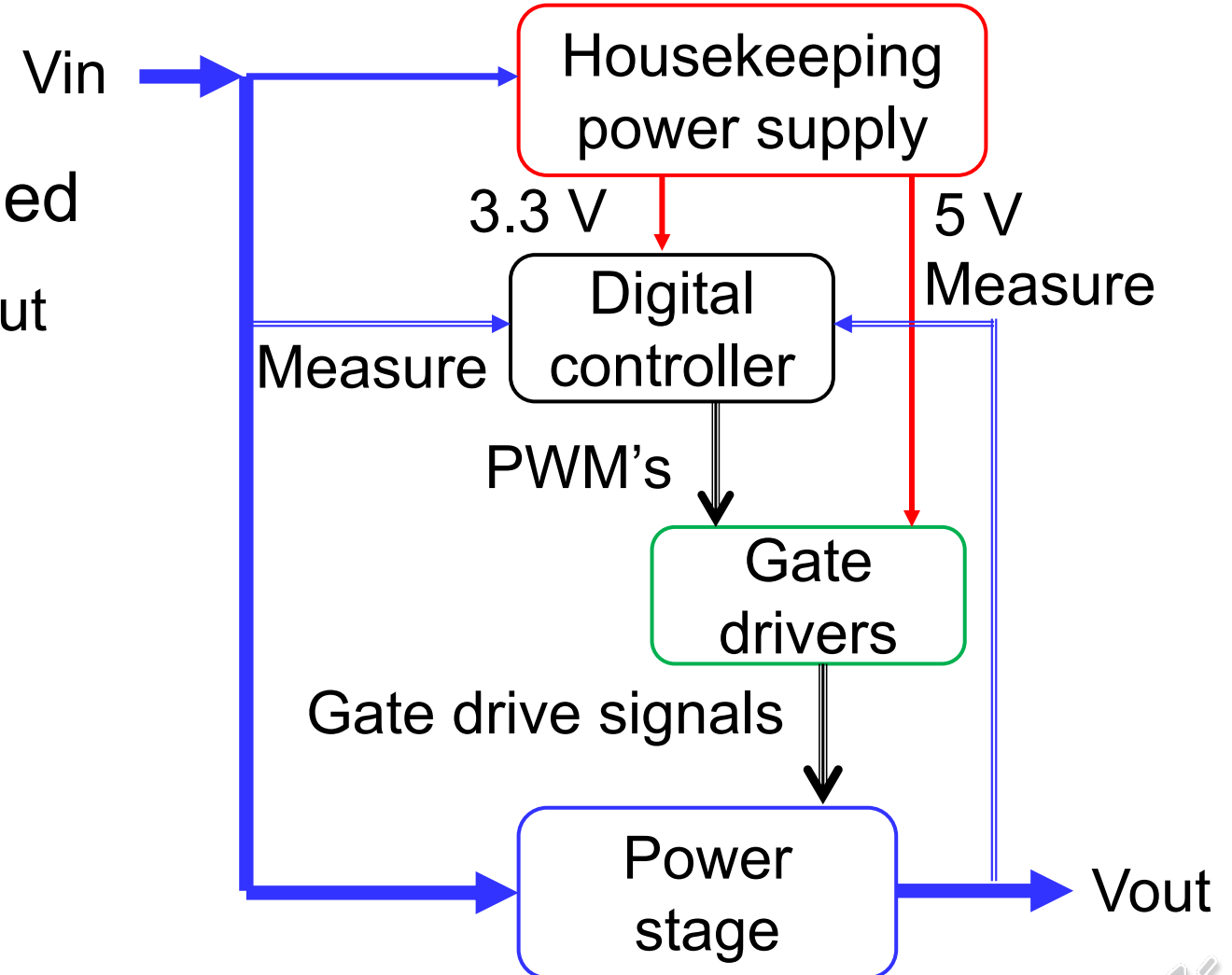
Topology	Buck Converter	Switched Capacitor	LLC converter
Load regulation	Full regulation	Fixed even-ratio with large high-current droop	Fixed ratio, low droop
Power density	Medium	Medium	High
Efficiency	$\approx 97\%$	$\approx 98\%$	$\approx 98\%$
Load power	$< 300\text{ W}$	$< 600\text{ W}$	$> 300\text{ W}$
Complexity	Simple	High	Medium



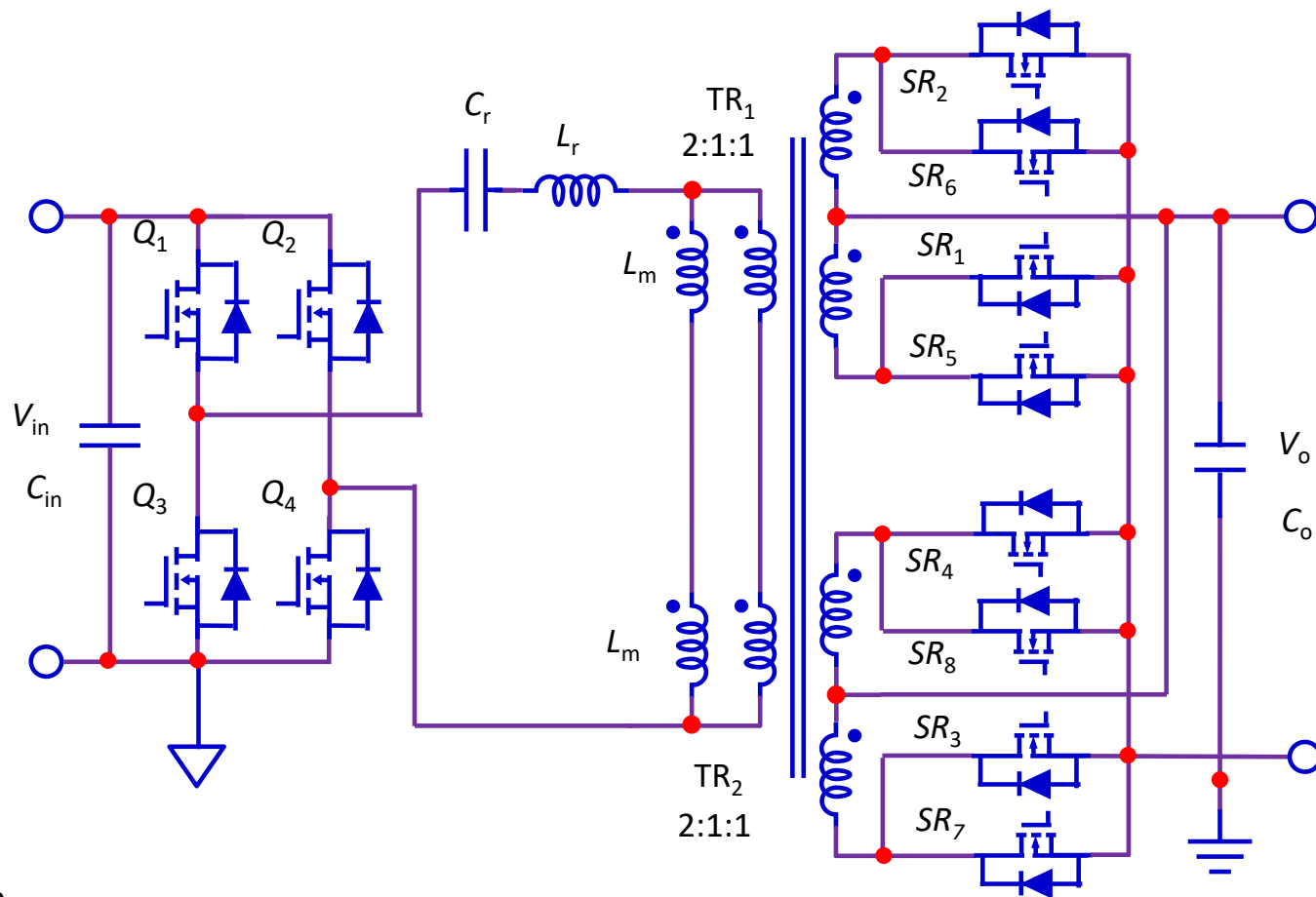
Module Design



- System needs to be self contained
 - Gate power derived from 48 V input
 - 3.3 V power derived from 5 V
- Digital controller
 - Voltage feedback control
 - Precise timing

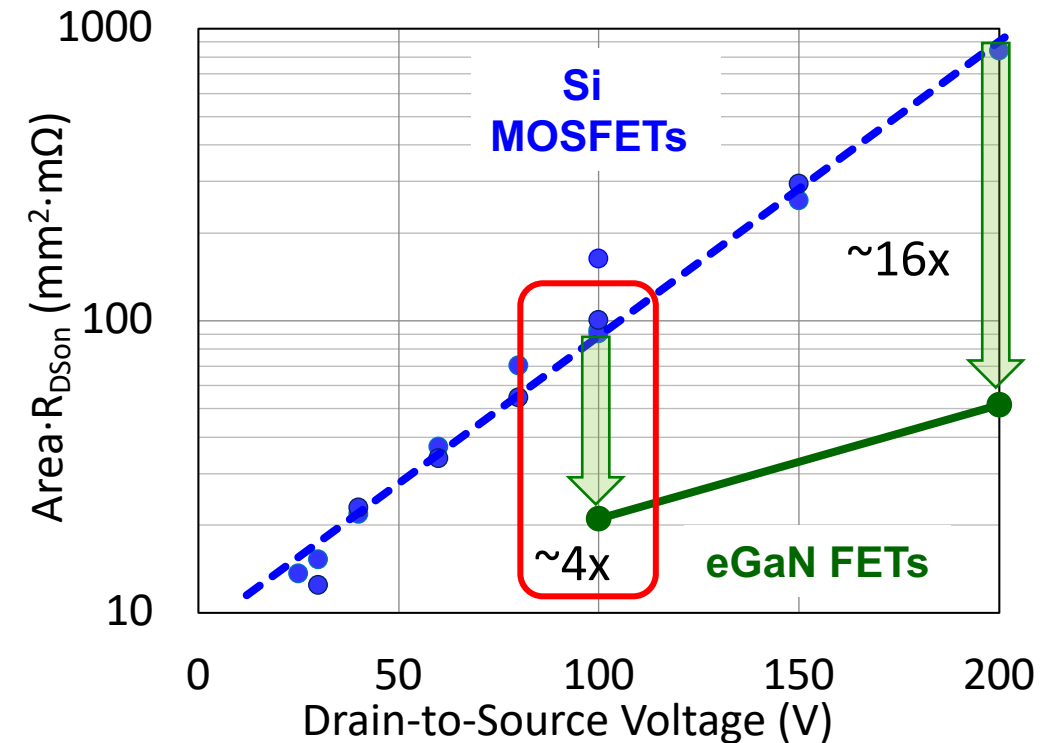
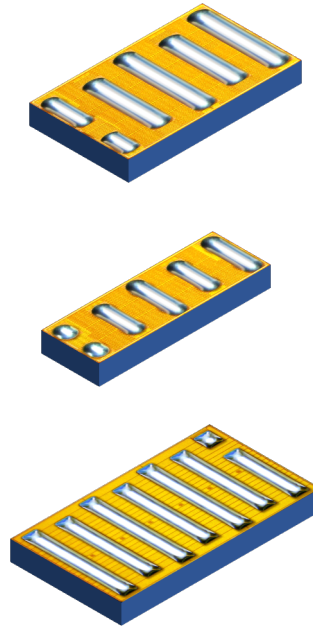


- Full bridge primary
- Lower primary current
- No DC voltage across resonant capacitor
- Leakage inductance used for resonance
- Magnetizing inductance used for ZVS
- Dual rectifier secondary
- High Current
- Parallel FETs
- Dual center tap common ground FETs



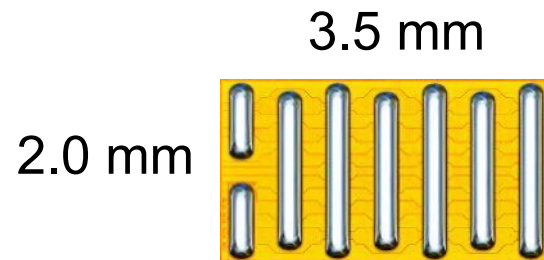
With respect to MOSFETs:

- Reduced FOM ~ 4 times
- Lower Q_G ~ 5 -10 times
- Lower R_{DSon} at $V_{GS} = 5 V$
- Lower Q_{OSS}
- Lower Q_{GD}
- Zero Q_{RR}
- Smaller



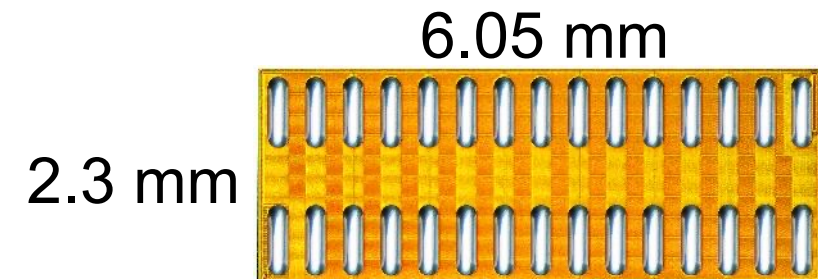
Primary Side

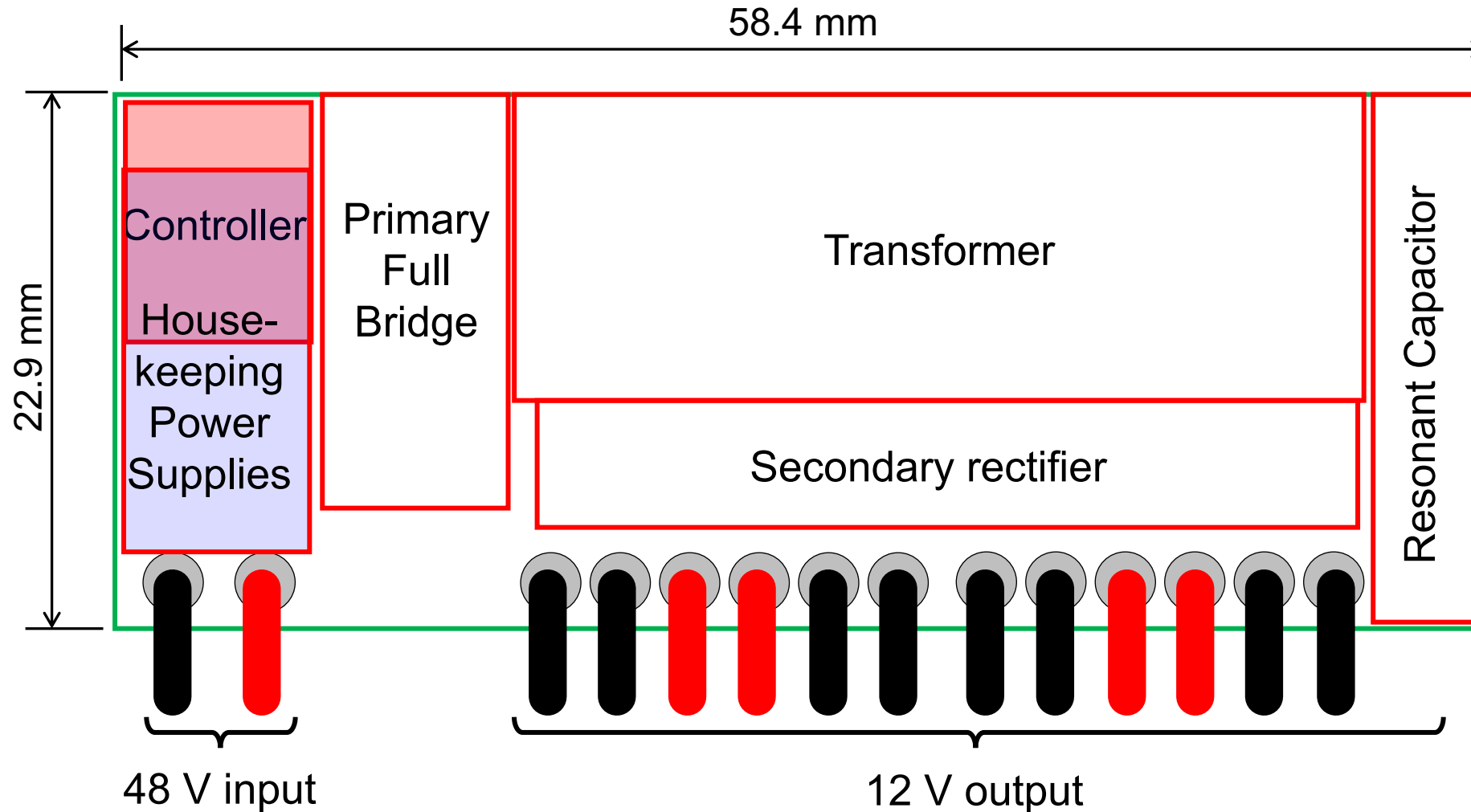
Parameter	EPC2218
$V_{ds,max}$	100 V
$R_{ds,on}$	2.4 m Ω
Q_{oss}	46 nC
Q_G	10.5 nC
$R_{\theta,jc}$ $R_{\theta,jb}$	0.5 °C/W 1.4 °C/W



Secondary Side

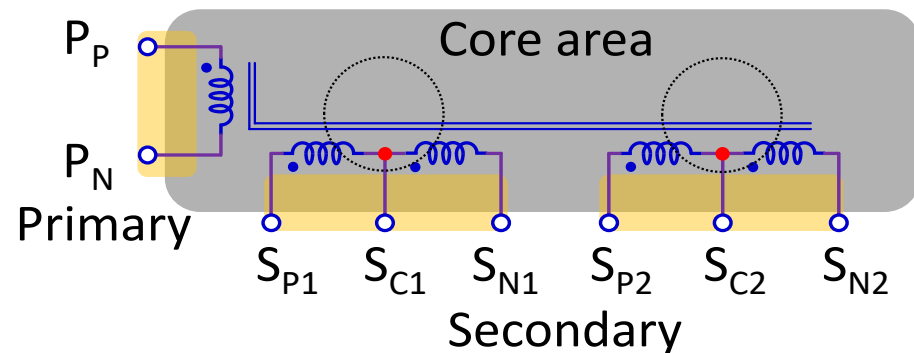
Parameter	EPC2024
$V_{ds,max}$	40 V
$R_{ds,on}$ at 4.5 V _{GS}	1.2 m Ω
Q_{oss}	45 nC
Q_G	18 nC
$R_{\theta,jc}$ $R_{\theta,jb}$	0.4 °C/W 1.1 °C/W



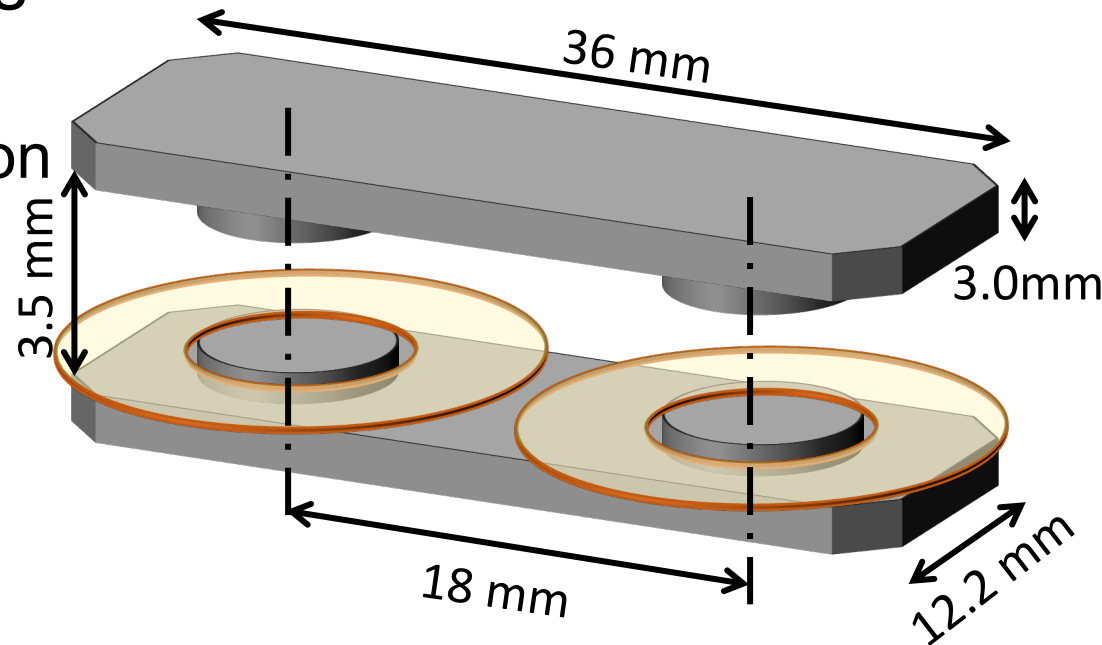


Transformer Design Overview

- 3 oz Copper thickness windings
- Interleaved windings for min. loss
- Minimize power path losses
 - Primary side connection
 - Secondary bottom connection



Transformer
connection points

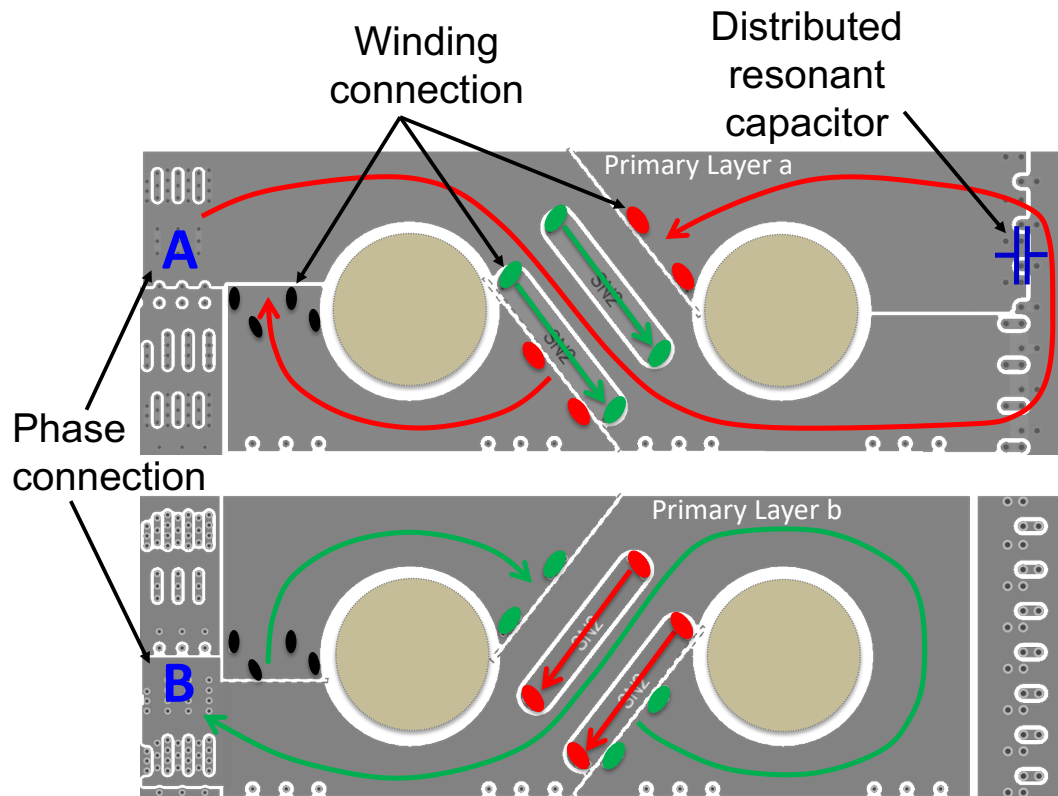


Layer Stackup

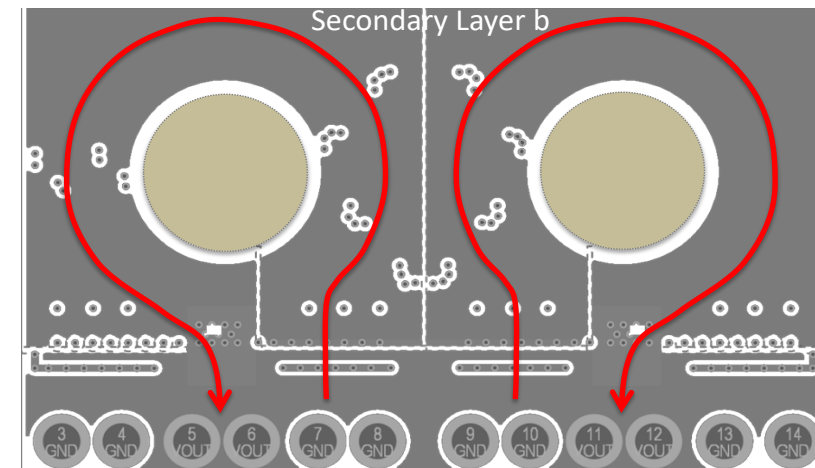
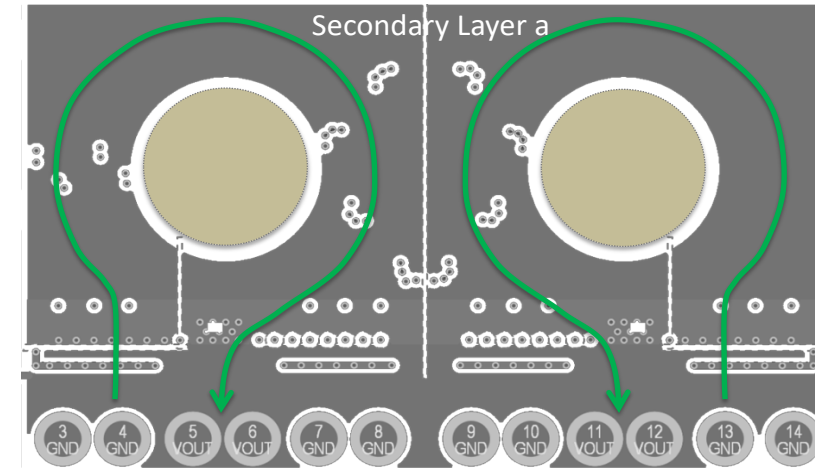
1	Shield
2	Sec-
Pri 3	
4	Sec+
5	Sec+
Pri 6	
7	Sec-
8	Sec-
Pri 9	
10	Sec+
11	Sec+
Pri 12	
13	Sec-
14	Shield



- Primary winding cross-over
- Short secondary connections



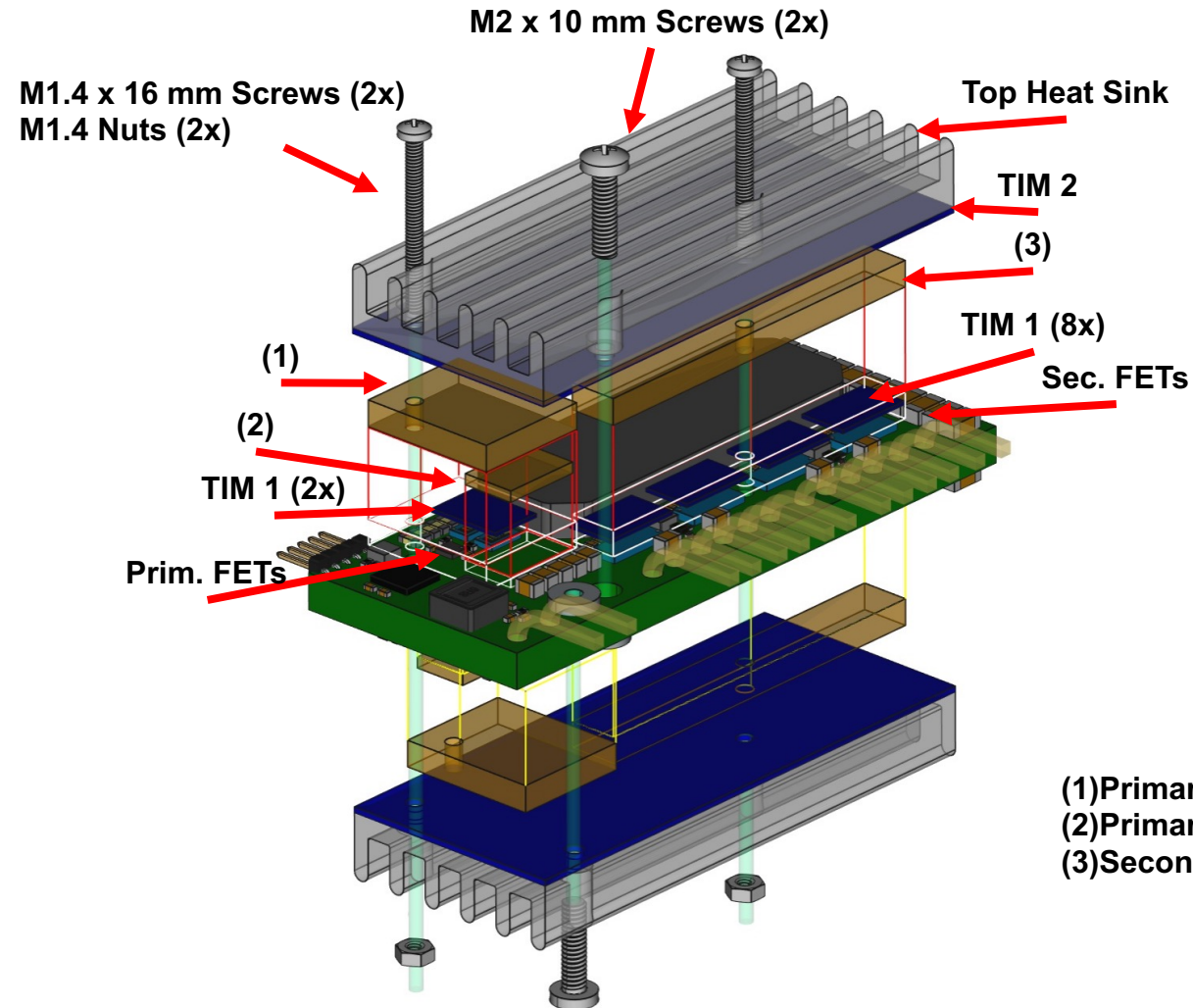
Primary winding design



Secondary winding design

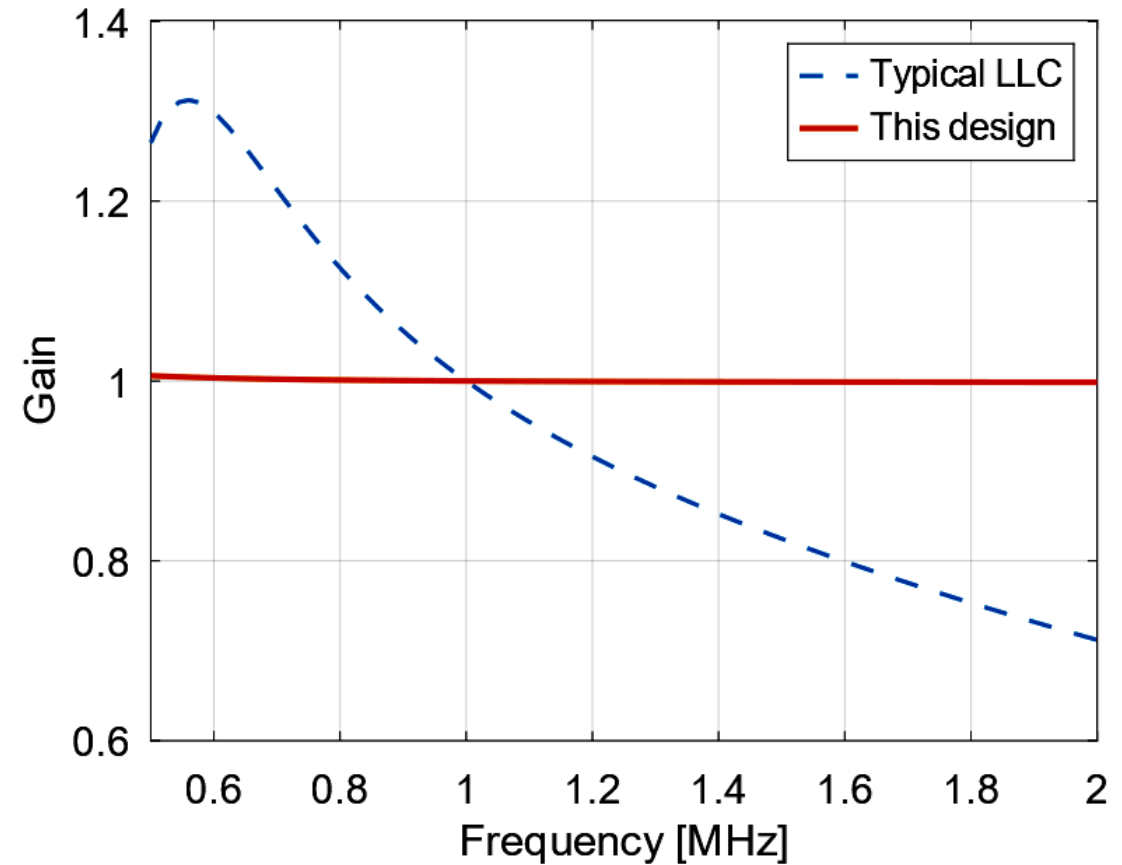


- Customized heat spreaders
- TIM used for improving thermal conductivity
 - T-Global: A1780- 500 μm for FETs (TIM 1)
 - High thermal conductivity (17.8 W/m.K)
 - Compressible (2:1)
 - Isolation
 - T-Global: A6300 used for Heat Sink (TIM 2) (6.2 W/m.K)



- (1) Primary Heat Spreader (2x)
- (2) Primary Heat Spreader Seat (2x)
- (3) Secondary Heat Spreader (2x)

- Resonant inductance, transformer leakage, very small $\sim 8\text{nH}$. Frequency modulation not possible
 - Startup current limit achieved using PWM ramp up – 2% – 50%
- Over-temperature protection



Voltage conversion ratios of a typical LLC converter compared to this design.



Experimental Validation



Programming
& Comms
Port

Primary HB 1
EPC2218's

Resonant Capacitor Bank:
Ultra low ESR, Voltage stable

Controller

Transformer

- Embedded in PCB
- ML91S core

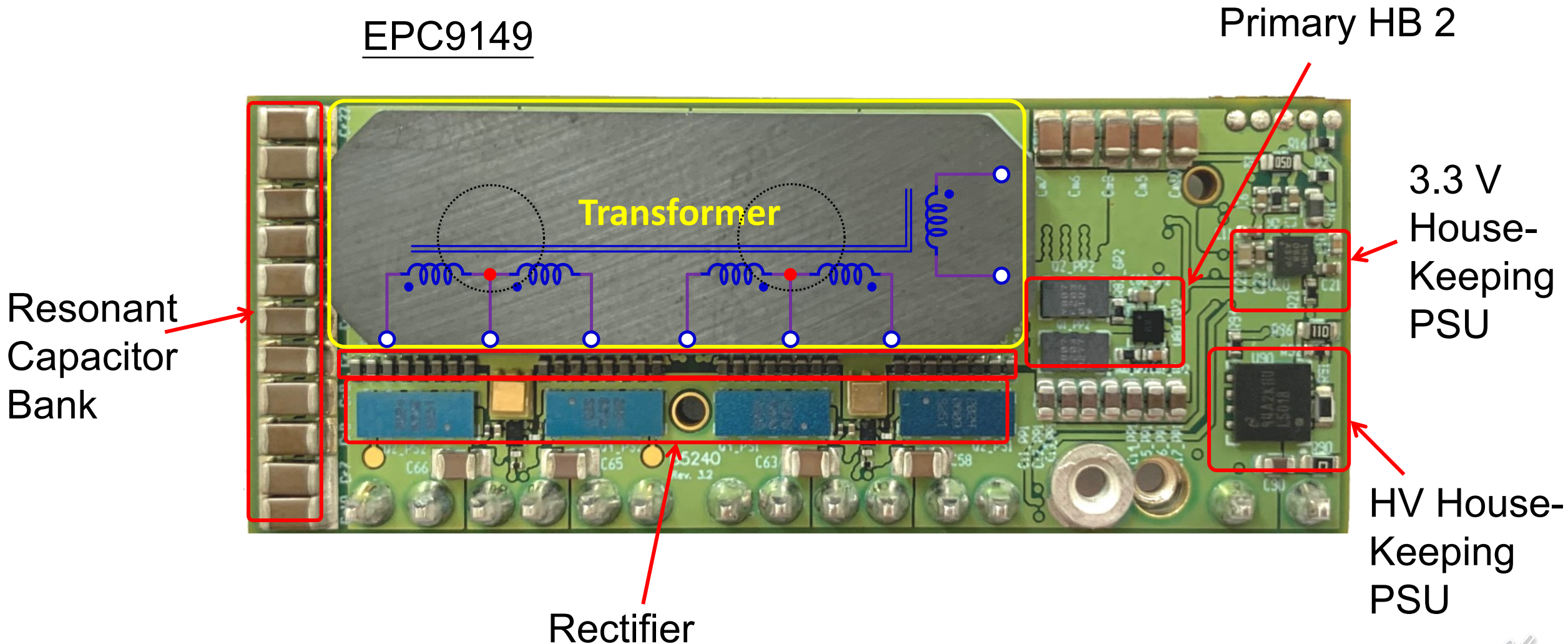
HV House-
Keeping PSU

Output
Capacitors

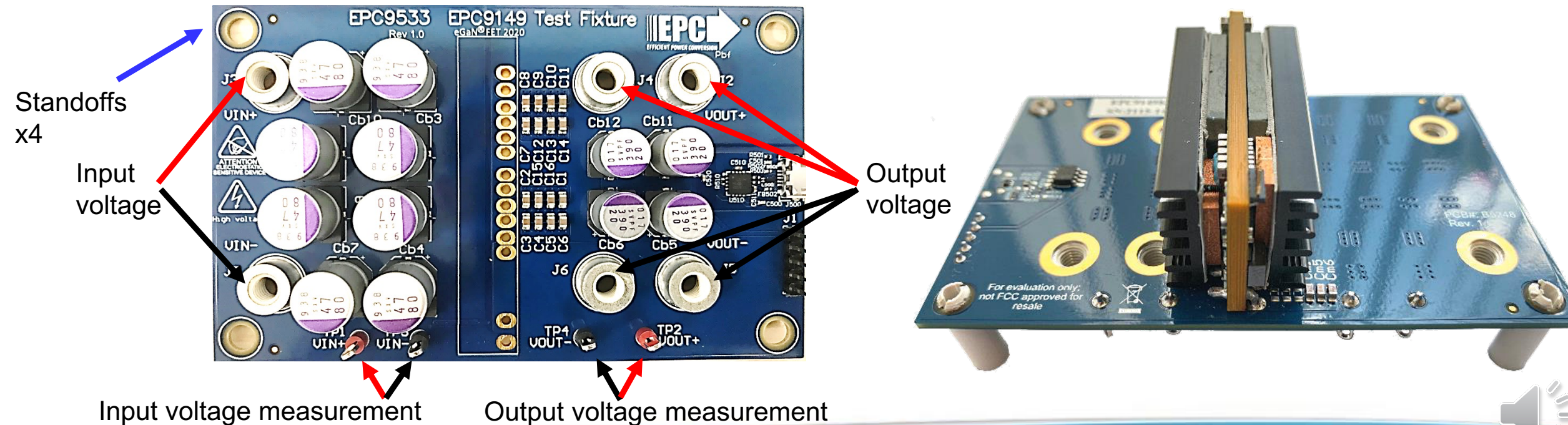
Input Capacitors

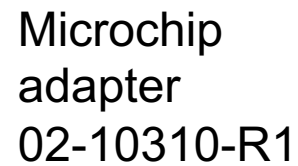
Rectifier
EPC2024's

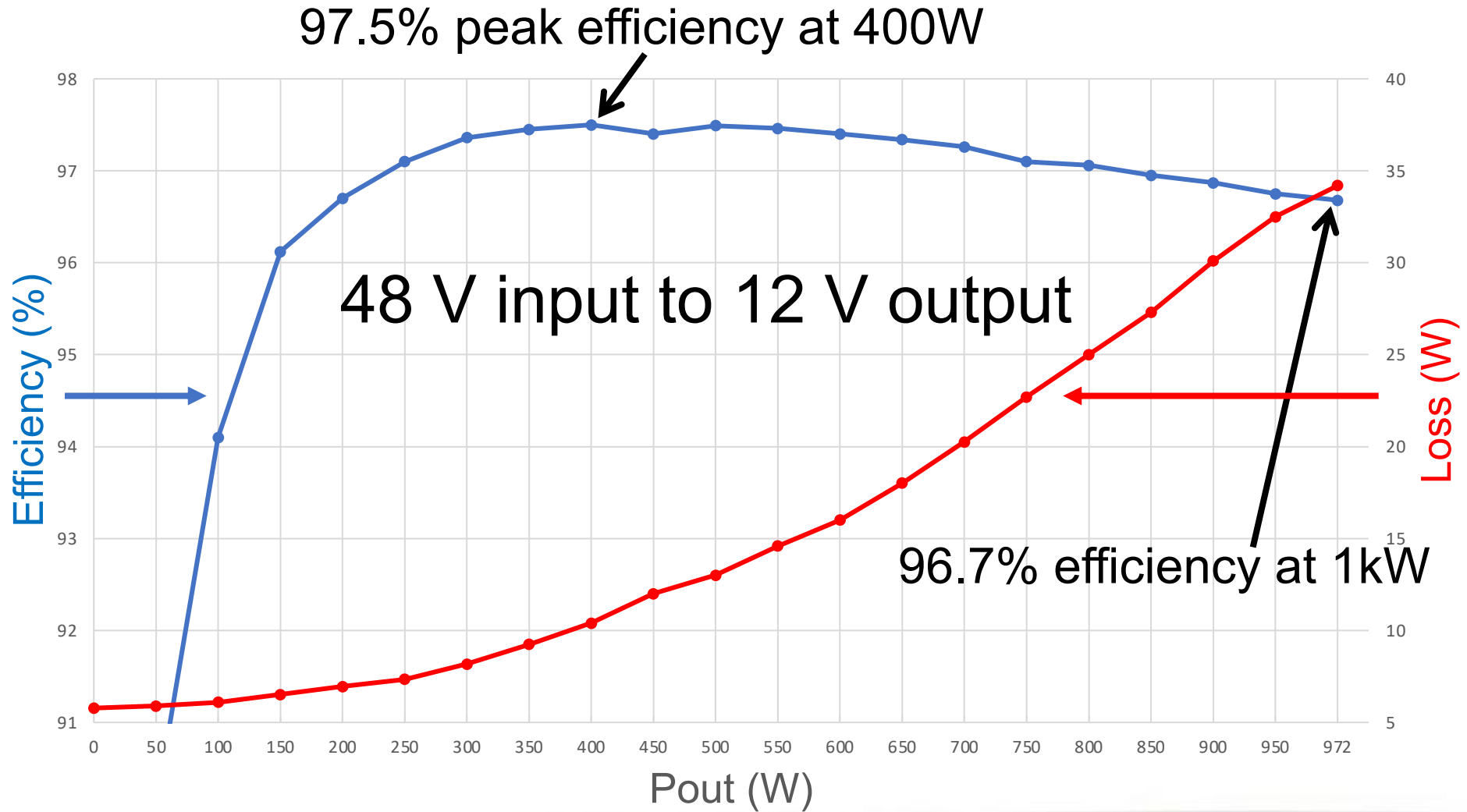
EPC9149



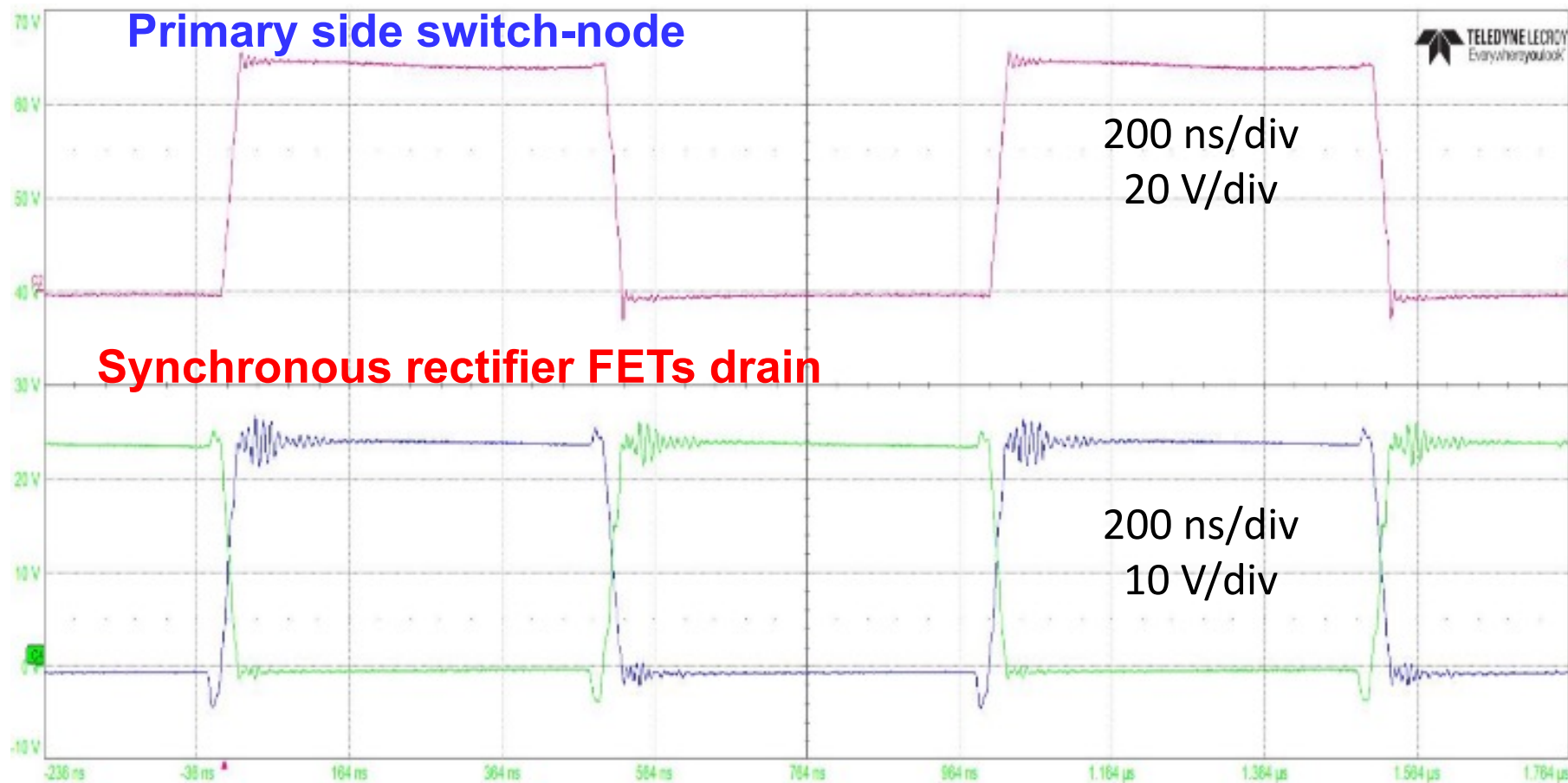
- Input and output connections,
- Kelvin measurement:
 - Input and output Voltage
- The LLC module is soldered on the motherboard.



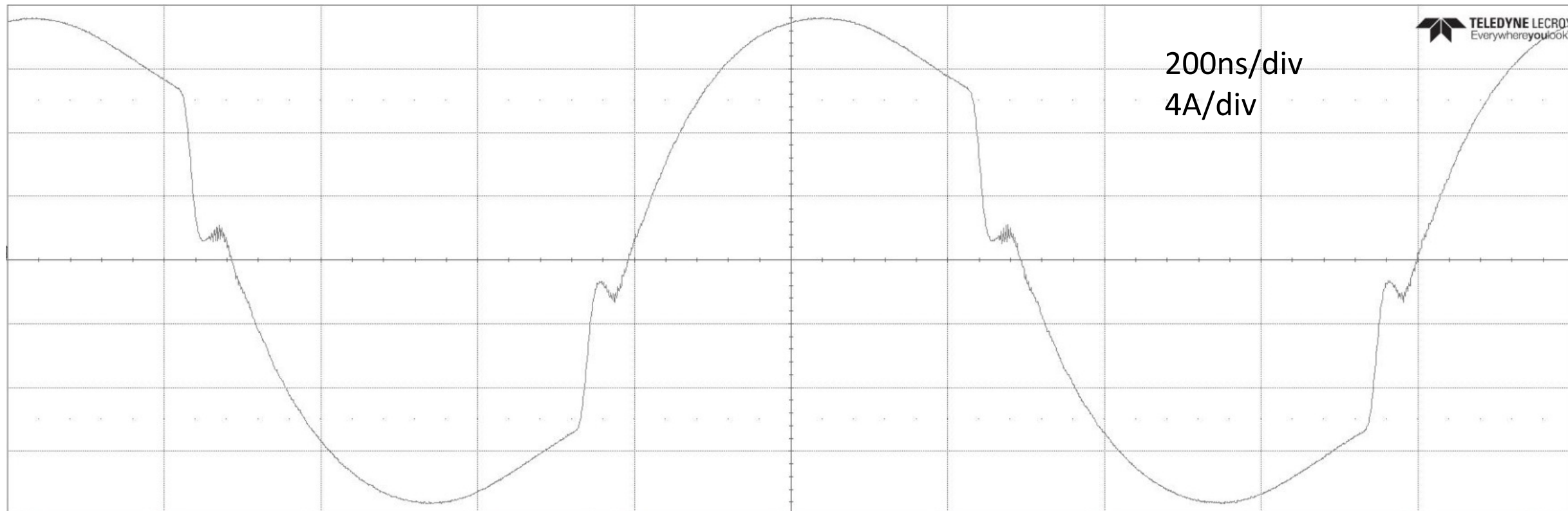


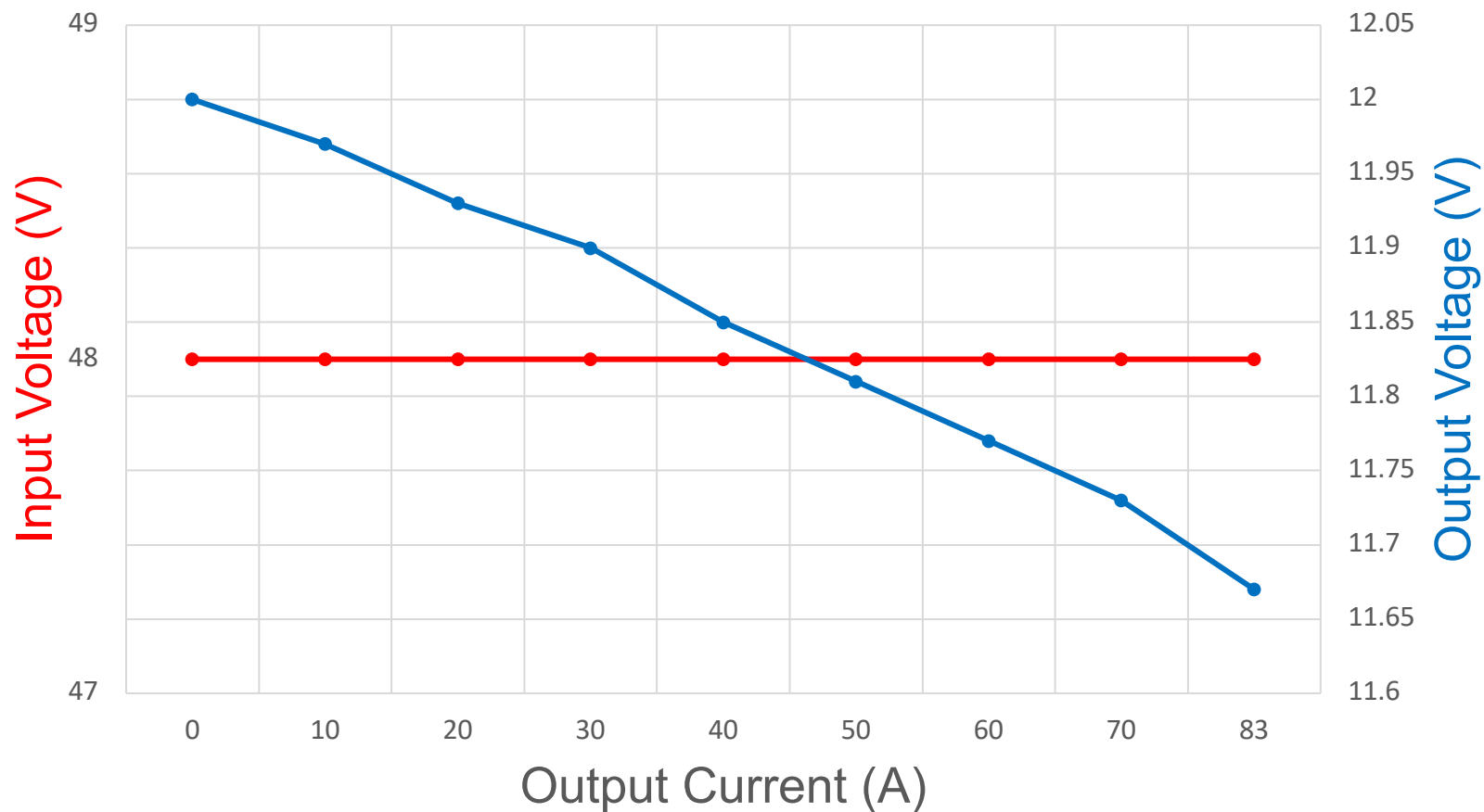


48 V input to 12 V output at 1kW



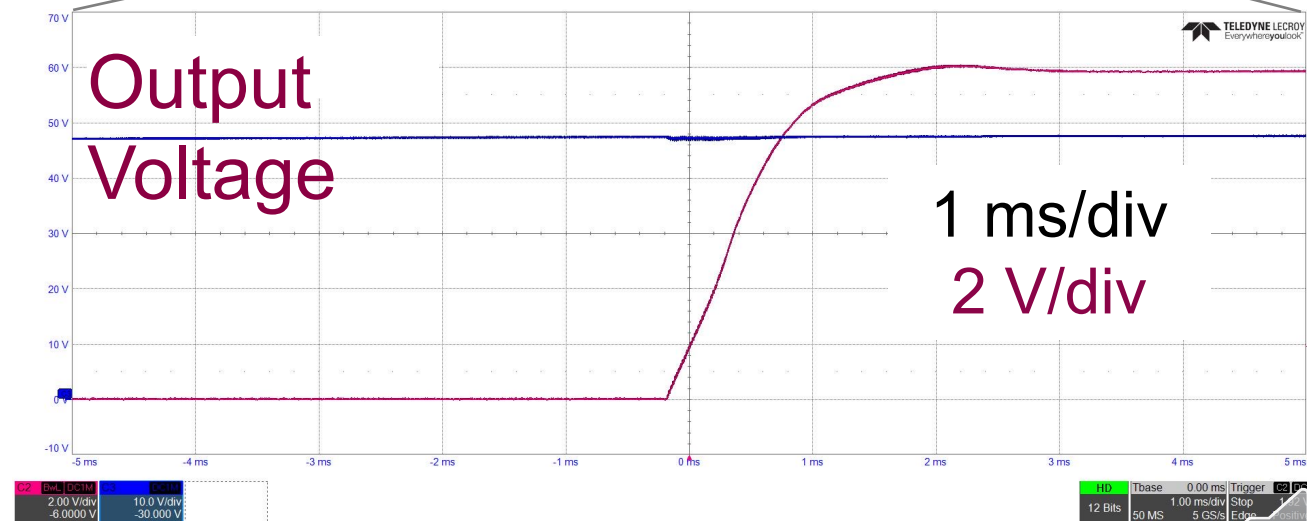
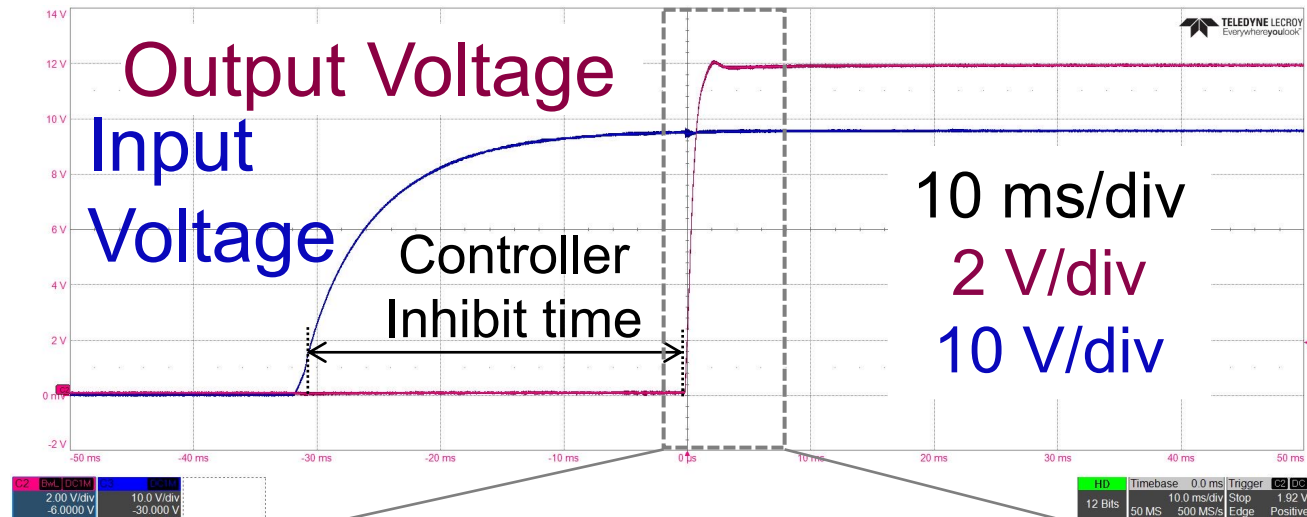
Primary Current





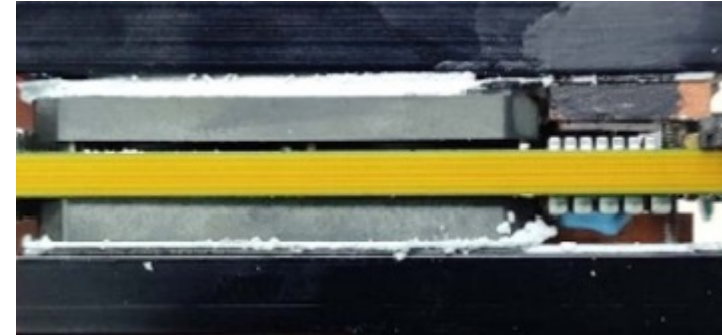
Output voltage droop vs output current

- Soft startup implemented:
 - Avoid inrush current and excessive voltage stress
 - Duty cycle ramp up
- Start into resistive load (144mΩ)

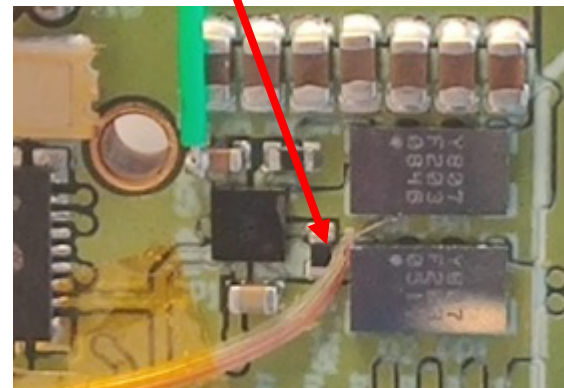


- FET die temperature measured using K-type thermocouple
- IR camera used to measure external temperature of board, HSp, and heatsink
- Forced convection cooled at 400 LFM
- Device operated at full load 83A

Top view of final assembled structure



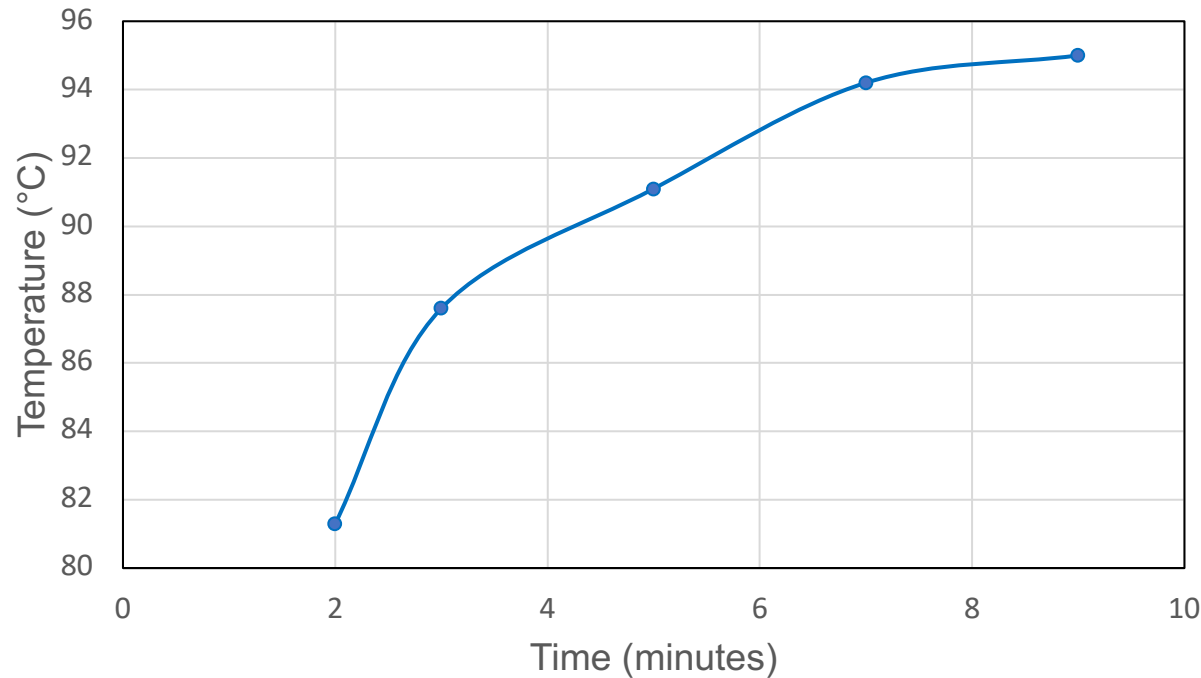
TC



Anemometer



- Steady state in 10 minutes
- 70 °C primary FETs rise

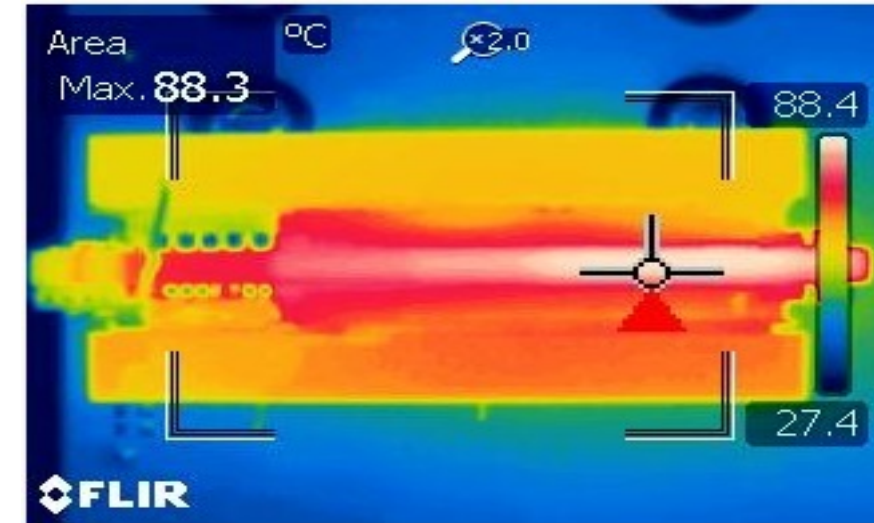


48 V_{IN}, 12 V_{OUT}, 1 kW, 400 LFM, T_{Amb} = 25°C

Board standard image

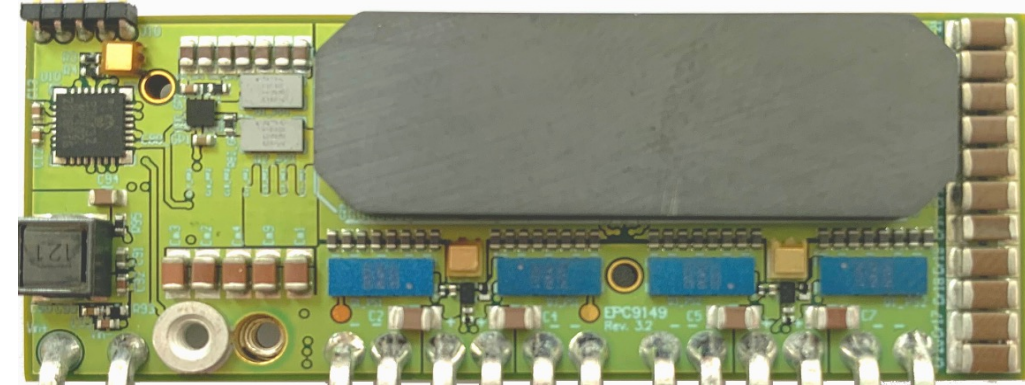


Air-Flow



Board thermal image

- 1 kW LLC design
 - 58.4 x 22.9 x 10 mm volume
 - Uses conventional PCB technology
- eGaN FETs
 - Achieves high efficiency
 - Enable high power density (1226 W/in³)



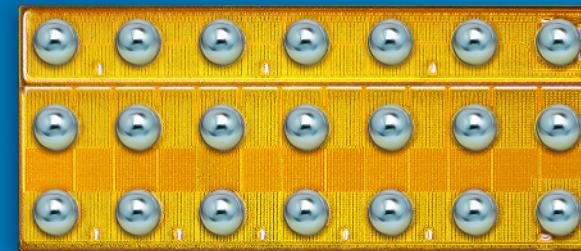


How To GaN Video Series

epc-co.com

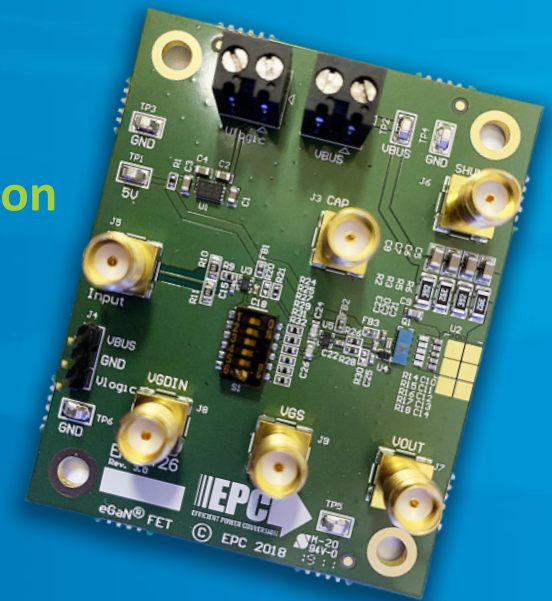


3rd Edition Textbook



eGaN[®] FETs and ICs

Evaluation
Kits



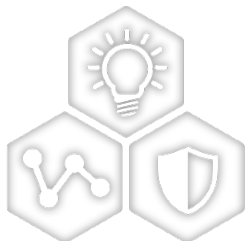
Microchip Solution On EPC9149 LLC Converter



A Leading Provider of Smart, Connected and Secure Embedded Solutions



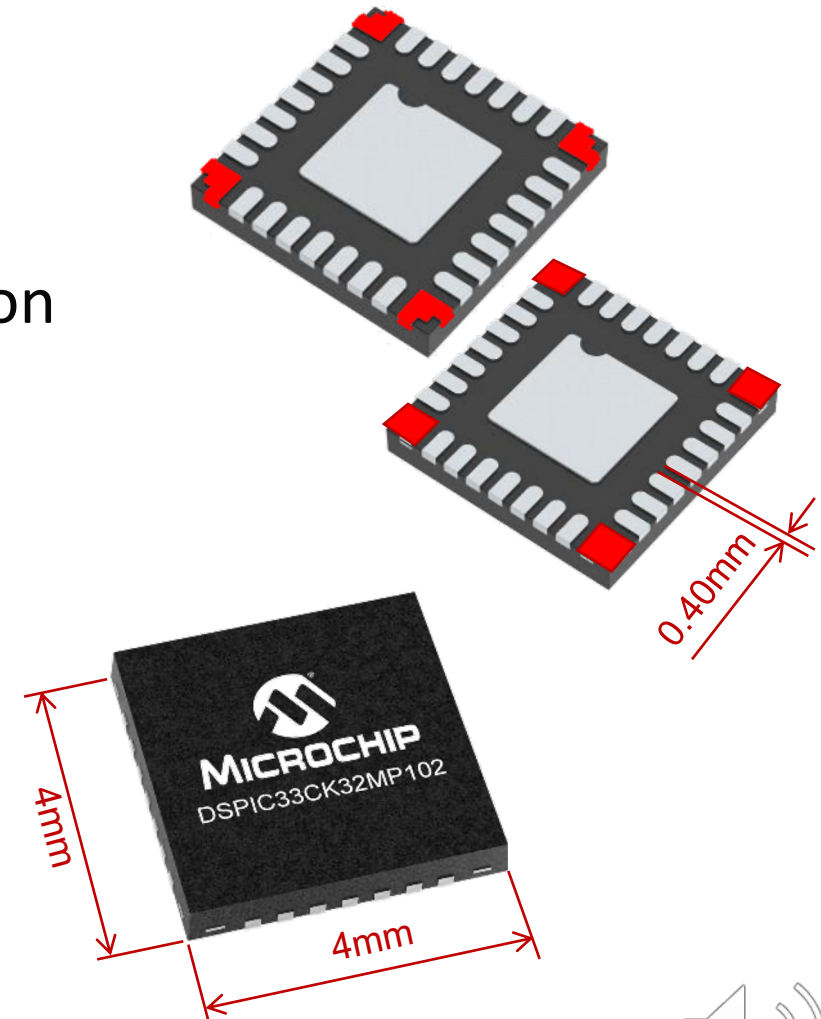
Edward Lee
Dec. 2nd, 2021



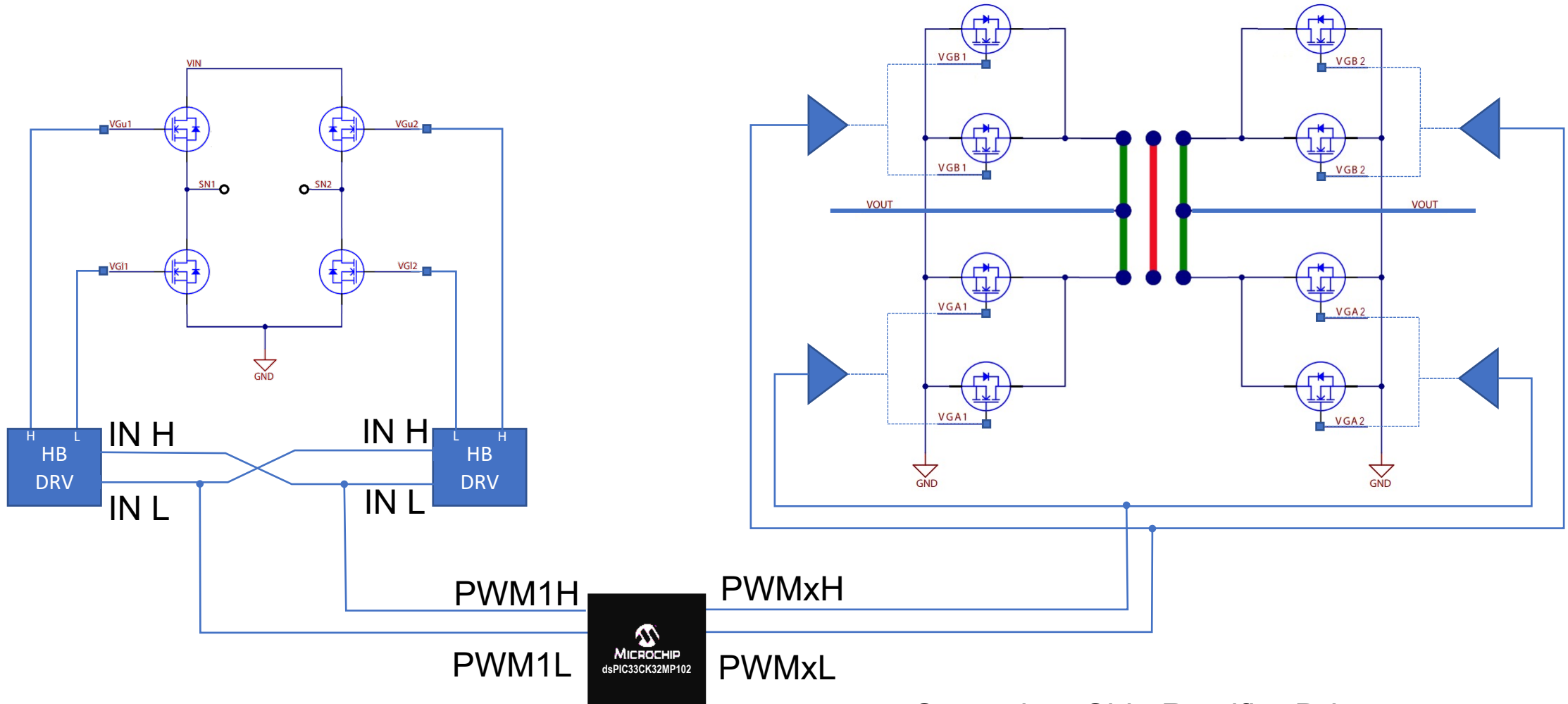
2021 Microchip 高效能電源技術線上研討會

Controller Overview

- **Choice of controller dsPIC33CK32MP102T-I/M6**
 - Very small at 4x4 mm
 - 250ps PWM resolution for precise ZVS timing
 - Low power consumption
 - Built in Op-Amps for analog feedback circuit reduction
- **Controller used for**
 - Maintaining ZVS
 - De-embed gate drive propagation mismatch
 - Power flow direction
 - Startup PWM
 - Operations monitoring
 - Over temperature protection
 - Communications



PWM Drive Simplification

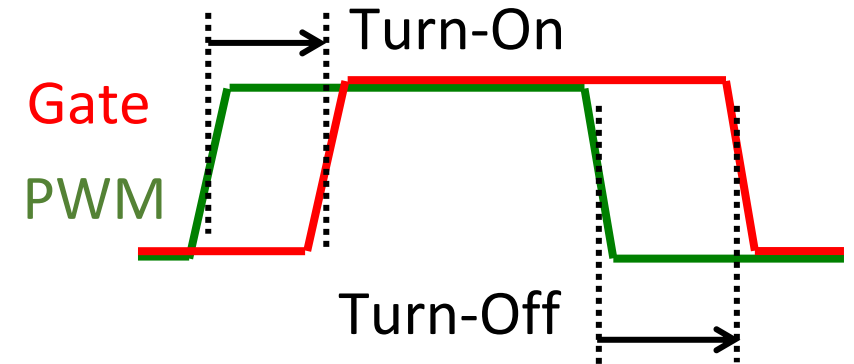


Primary Side Full Bridge Drive

Secondary Side Rectifier Drive

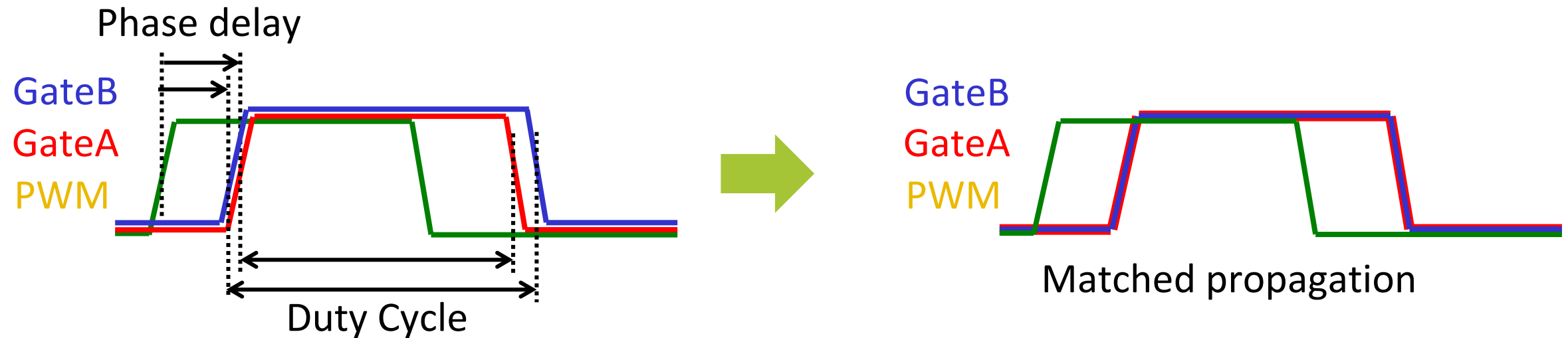
Key PWM Adjustment Settings

- **Correcting gate driver propagation delay mismatches**
 - Within gate driver mismatch
 - Between gate driver's mismatch
 - Between gate driver types mismatch (Pri-Sec)
- **Propagation mismatch**
 - Generates DC offset
 - Asymmetrical current and even harmonic generation
- **Settings**
 - Optimal timing for ZVS
 - Optimal operating frequency
 - Overcomes discrete capacitor values



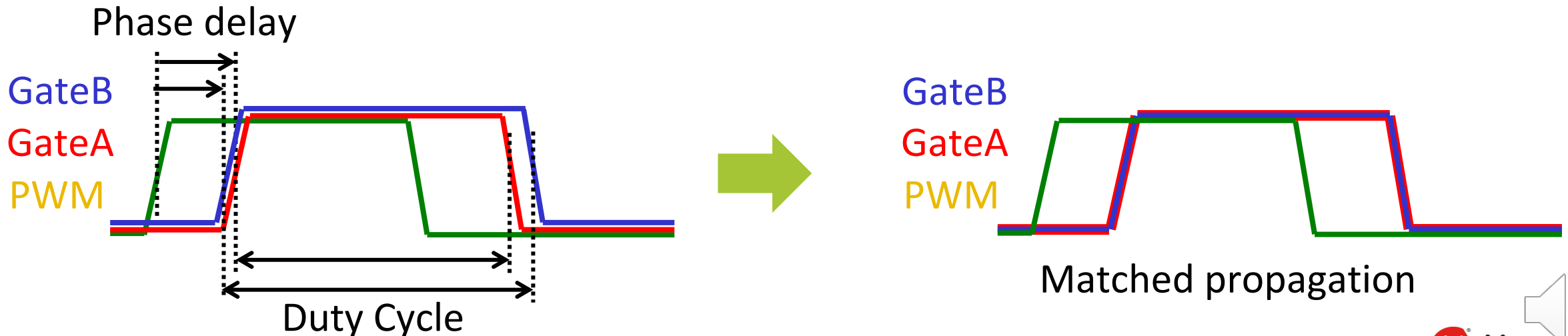
Primary Side Timing

- Phase delay – compensates driver to driver mismatch
- Duty cycle – compensates within a HB driver mismatch
- Dead-time – Sets ZVS (all 4 FETs will have same value)



Secondary Side Timing

- **Phase delay**
 - Compensates between primary and secondary drivers
- **Duty cycle**
 - Corrects gate driver mismatch
 - Sets correct timing of secondary

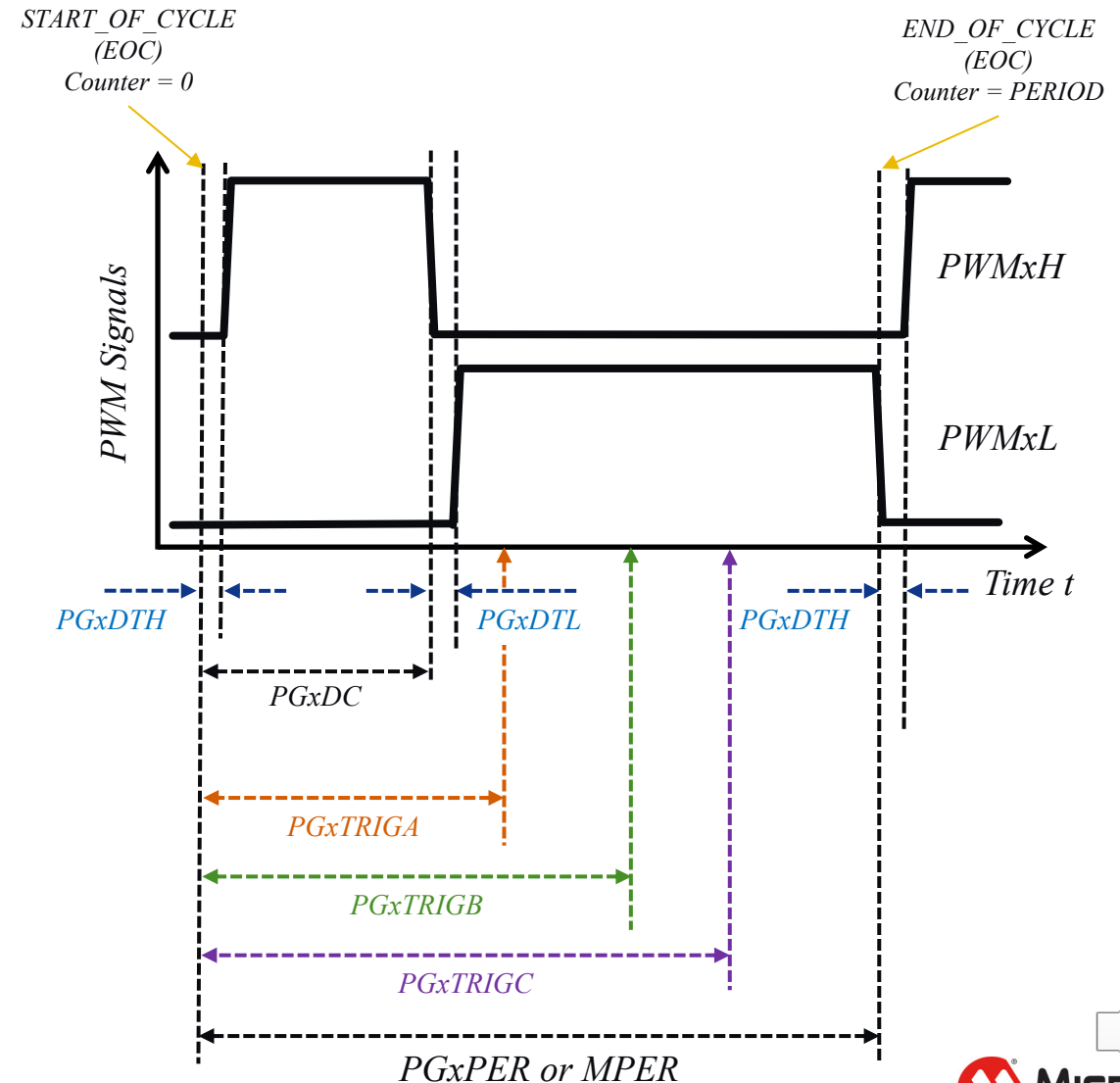


PWM Logic Programmability

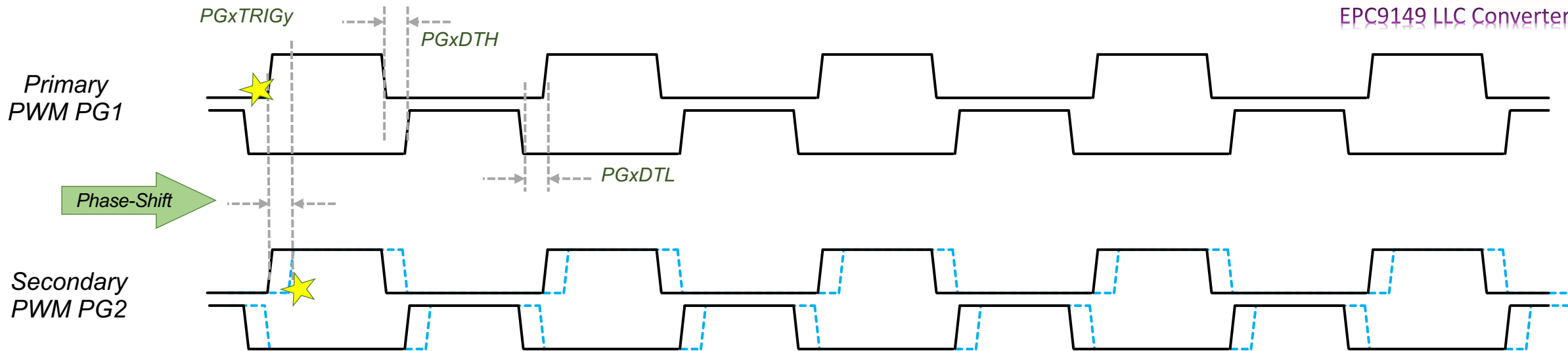
- Each PWM generator offers three triggers:

- PGxTRIGA:
 - Enhanced trigger options (can be delayed and shifted across multiple PWM cycles)
 - Available as ADC trigger
 - Available for PWM synchronization
- PGxTRIGB:
 - Generated each cycle (fixed)
 - Available as ADC trigger
 - Available for PWM synchronization
- PGxTRIGC:
 - Generated each cycle (fixed)
 - Available as ADC trigger
 - Available for PWM synchronization

- Each trigger can be placed across the cycle independently with 250 ps placement resolution

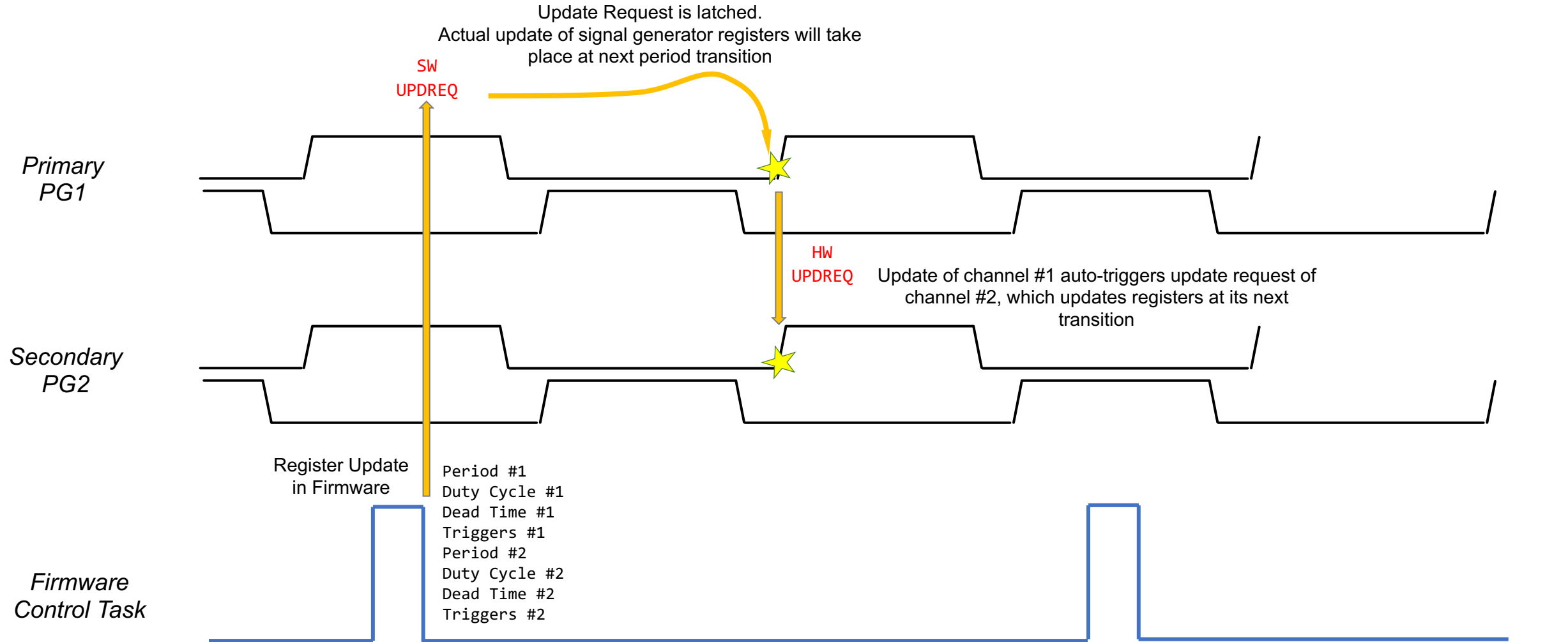


PWM Daisy Chain Configuration



- **Start-of-Cycle (SOC) of PWM channel PG2 is synchronized by PWM channel PG1 its trigger placed within its period at $PGxTRIGy$**
- **Each PWM channel remains fully configurable for individual duty cycles, dead times, periods, triggers etc.**
- **Frequency changes are applied to both channels simultaneously due to the synchronization trigger. All other properties, however, must be set by updating all desired registers independently**

Daisy chain update



Control Implementation

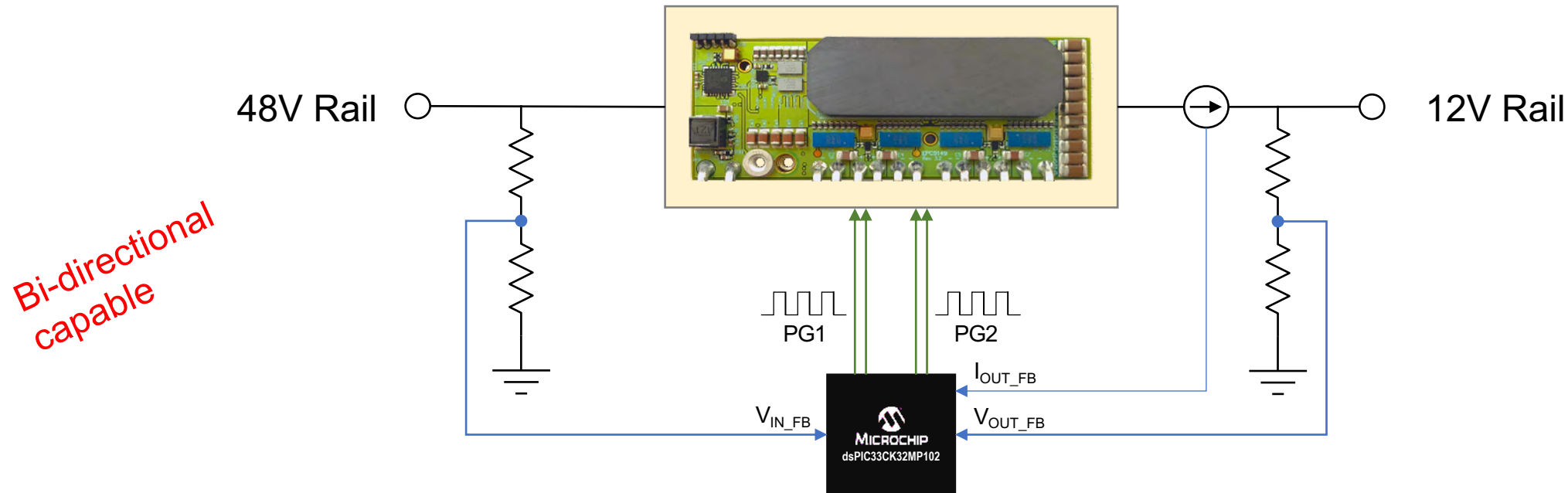
Operating Frequency Control:

- 4:1 conversion rate kept constant by VIN to VOUT comparison
- Continuous voltage monitoring of input and output voltage (UVLO, OVLO, OVP)

Duty-Cycle Startup Procedure:

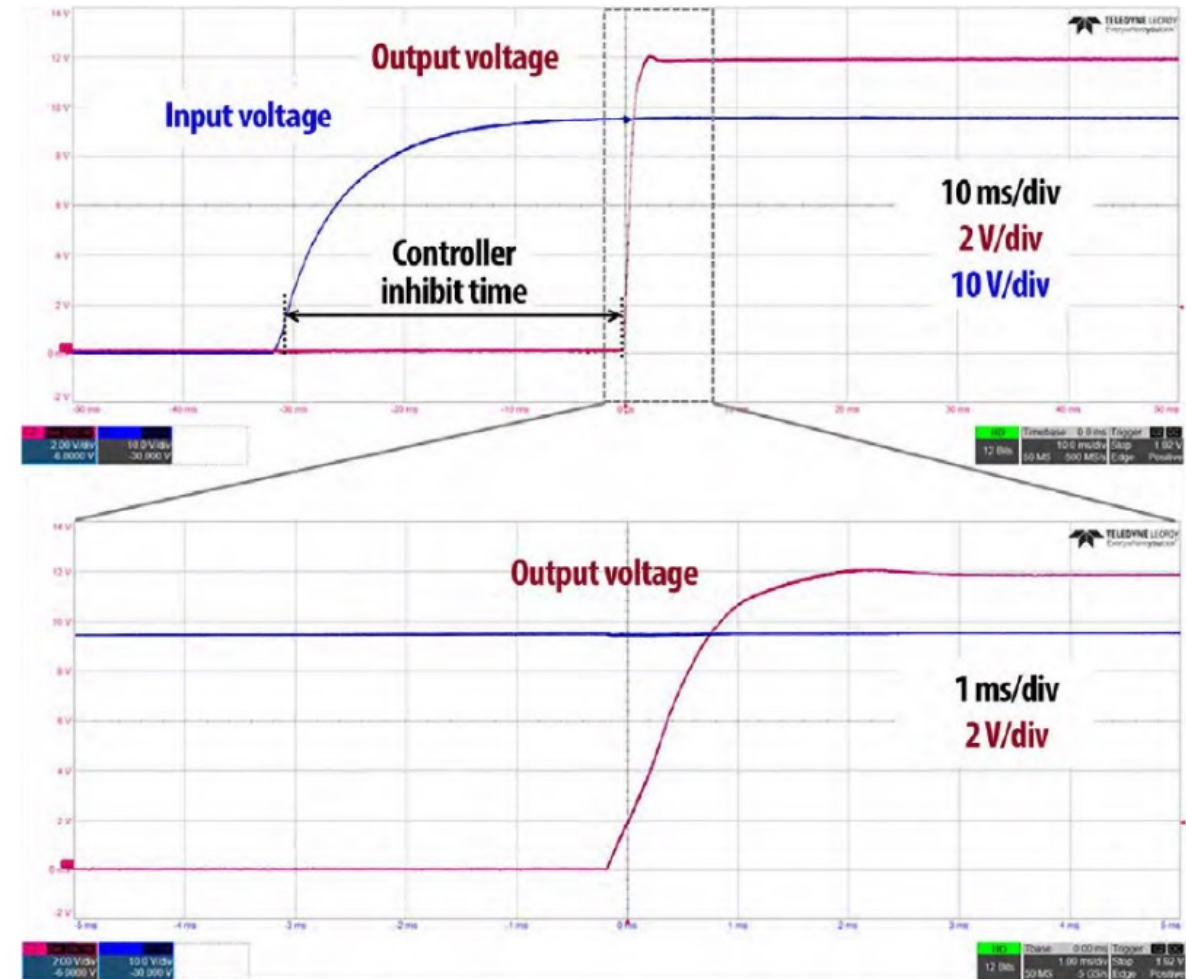
- Timer-controlled voltage ramp start-up keeping voltage growth monotonous
- Optimized pulse generation during duty cycle modulation for reduced component stress

4:1 Fixed Conversion Rate

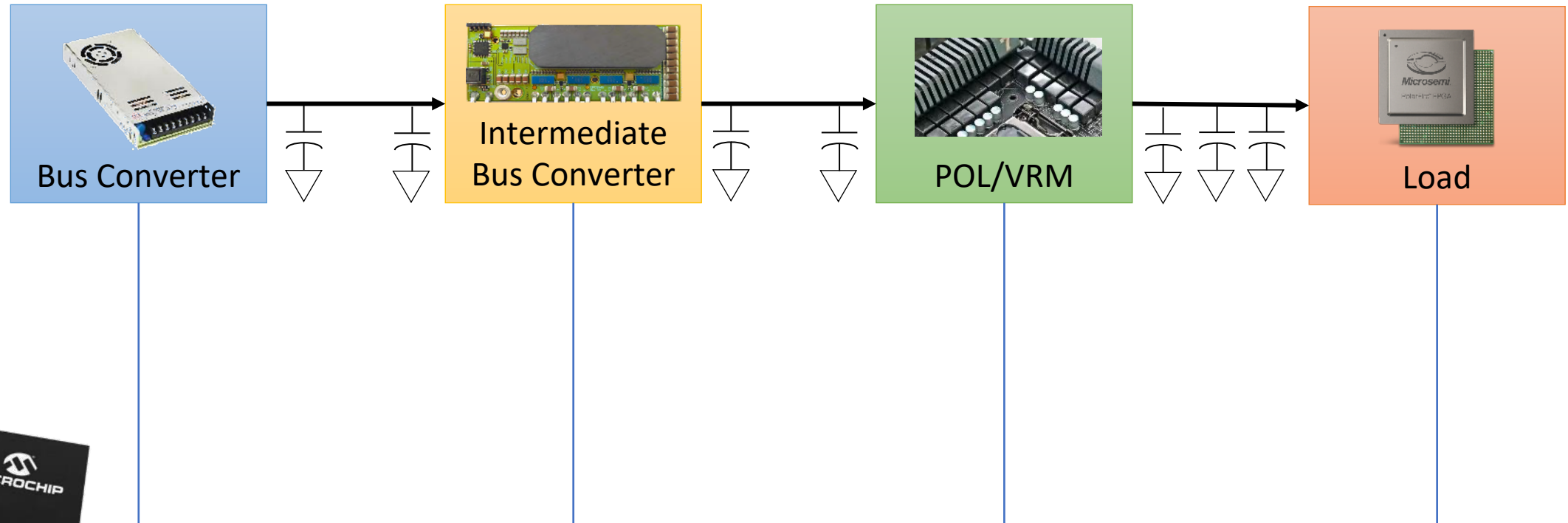


Startup

- Programmable output voltage ramp timing for advanced sequencing
- Monotonous startup
- Component stress reduction by optimized pulse generation based on voltage level and load current feedback

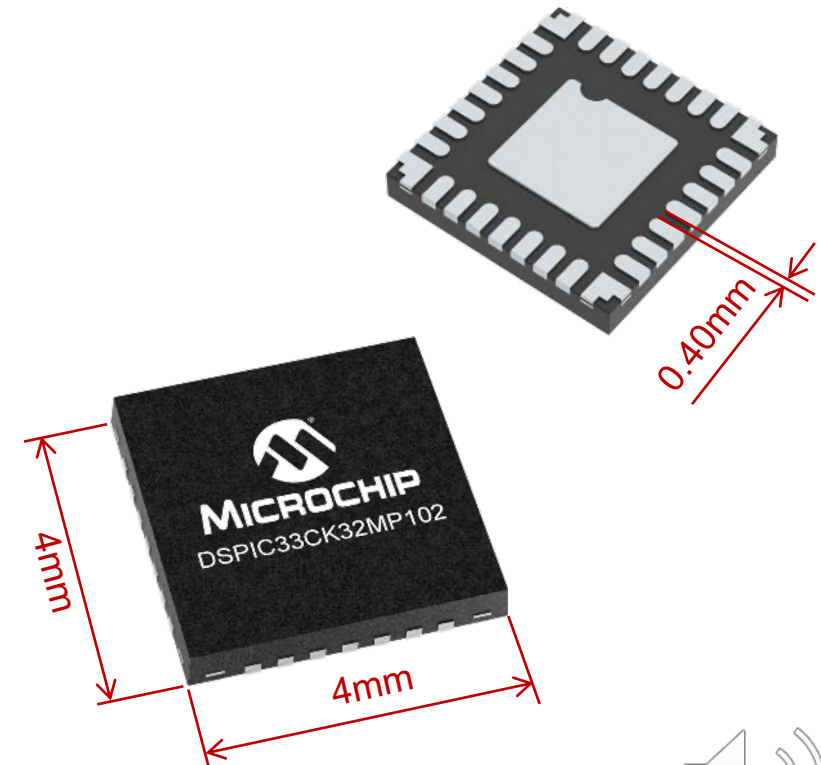
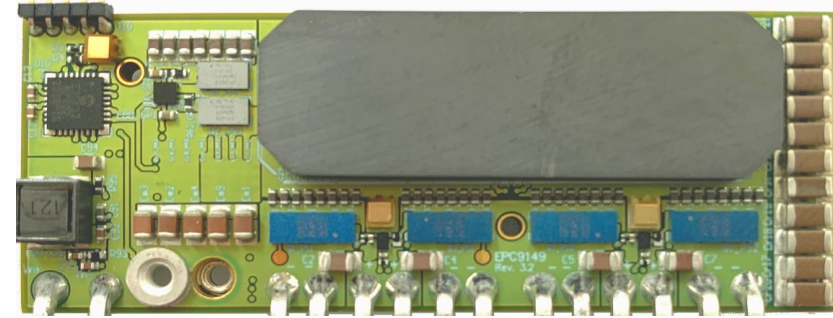


PDN System Design Considerations



Summary

- **1 kW LLC design**
 - 58.4 x 22.9 x 10 mm volume
- **eGaN FETs**
 - Achieves high efficiency
 - Enable high power density (1226 W/in³)
- **Propagation mismatches**
- **dsPIC33C**
 - PWM Logic Programmability
 - 250ps PWM resolution for precise ZVS timing
 - Very small at 4x4 mm





May The *Power* Be With You

